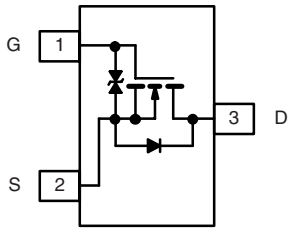
N-Channel 1.8-V (G-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (mA)
20	0.70 at V_{GS} = 4.5 V	600
	0.85 at V_{GS} = 2.5 V	500
	1.25 at V_{GS} = 1.8 V	350

SC-75A or SC-89



Top View

FEATURES

- **Halogen-free Option Available**
- TrenchFET® Power MOSFET: 1.8 V Rated
- Gate-Source ESD Protected: 2000 V
- High-Side Switching
- Low On-Resistance: 0.7 Ω
- Low Threshold: 0.8 V (typ.)
- Fast Switching Speed: 10 ns

Pb-free

RoHS COMPLIANT

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

BENEFITS

- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Battery Voltage Operation

ORDERING INFORMATION		
Part Number	**Package**	**Marking Code**
Si1012R-T1-E3 (Lead (Pb)-free) Si1012R-T1-GE3 (Lead (Pb)-free and Halogen-free)	SC-75A (SOT-416)	C
Si1012X-T1-E3 (Lead (Pb)-free) Si1012X-T1-GE3 (Lead (Pb)-free and Halogen-free)	SC-89 (SOT-490)	A

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V_{DS}	20		V
Gate-Source Voltage		V_{GS}	± 6		
Continuous Drain Current (T_J = 150 °C)[b]	T_A = 25 °C	I_D	600	500	mA
	T_A = 85 °C		400	350	
Pulsed Drain Current[a]		I_{DM}	1000		
Continuous Source Current (Diode Conduction)[b]		I_S	275	250	
Maximum Power Dissipation[b] for SC-75	T_A = 25 °C	P_D	175	150	mW
	T_A = 85 °C		90	80	
Maximum Power Dissipation[b] for SC-89	T_A = 25 °C		275	250	
	T_A = 85 °C		160	140	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C
Gate-Source ESD Rating (HBM, Method 3015)		ESD	2000		V

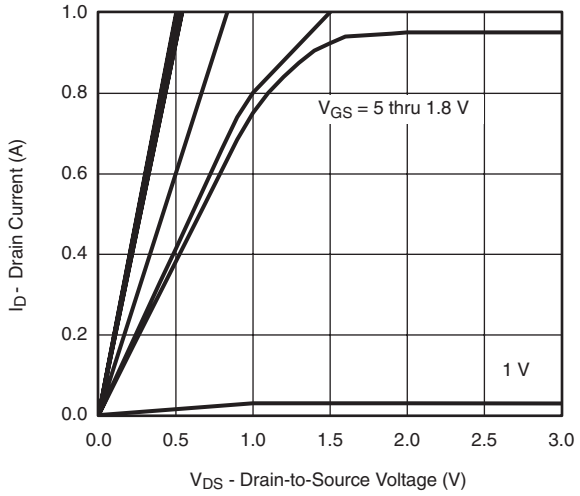
Notes:
a. Pulse width limited by maximum junction temperature.
b. Surface Mounted on FR4 board.

SPECIFICATIONS T_A = 25 °C, unless otherwise noted						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	0.45		0.9	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 4.5 V		± 0.5	± 1.0	µA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 20 V, V_{GS} = 0 V		0.3	100	nA
		V_{DS} = 20 V, V_{GS} = 0 V, T_J = 85 °C			5	µA
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 4.5 V	700			mA
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = 4.5 V, I_D = 600 mA		0.41	0.70	Ω
		V_{GS} = 2.5 V, I_D = 500 mA		0.53	0.85	
		V_{GS} = 1.8 V, I_D = 350 mA		0.70	1.25	
Forward Transconductance[a]	g_{fs}	V_{DS} = 10 V, I_D = 400 mA		1.0		S
Diode Forward Voltage[a]	V_{SD}	I_S = 150 mA, V_{GS} = 0 V		0.8	1.2	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 250 mA		750		pC
Gate-Source Charge	Q_{gs}			75		
Gate-Drain Charge	Q_{gd}			225		
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 10 V, R_L = 47 Ω I_D ≅ 200 mA, V_{GEN} = 4.5 V, R_G = 10 Ω		5		ns
Rise Time	t_r			5		
Turn-Off Delay Time	$t_{d(off)}$			25		
Fall Time	t_f			11		

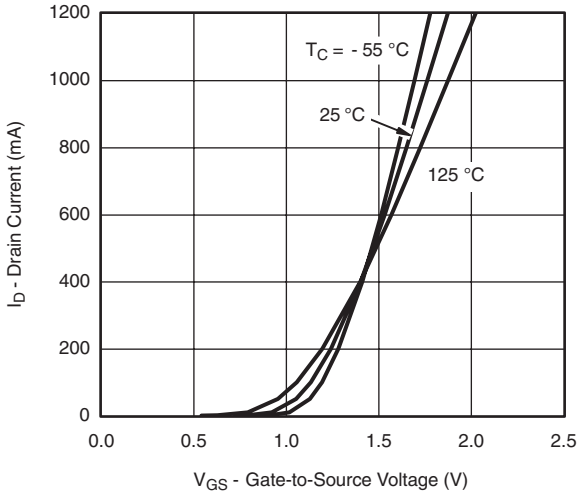
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

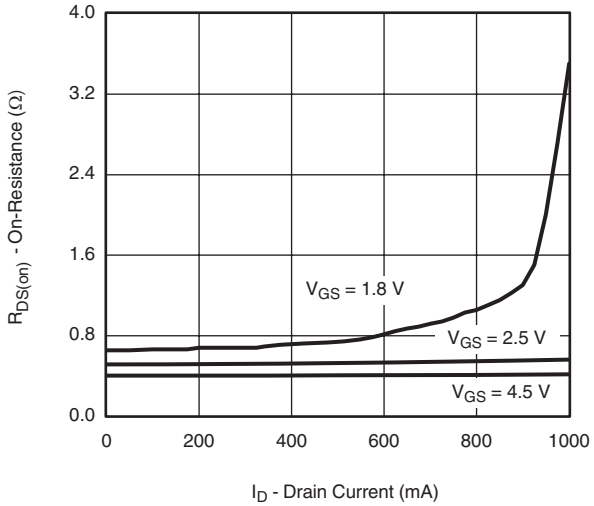
TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



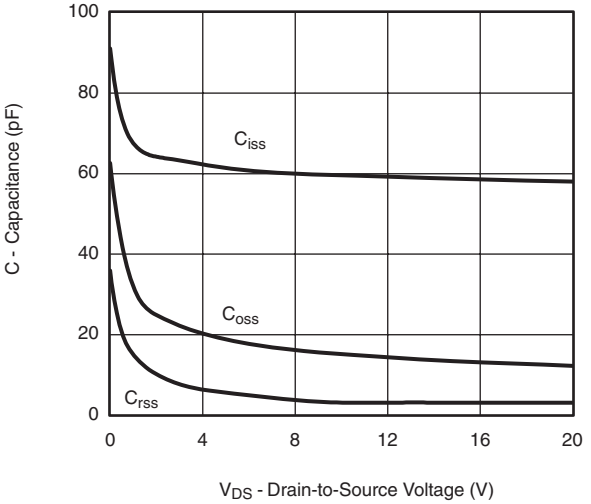
Output Characteristics



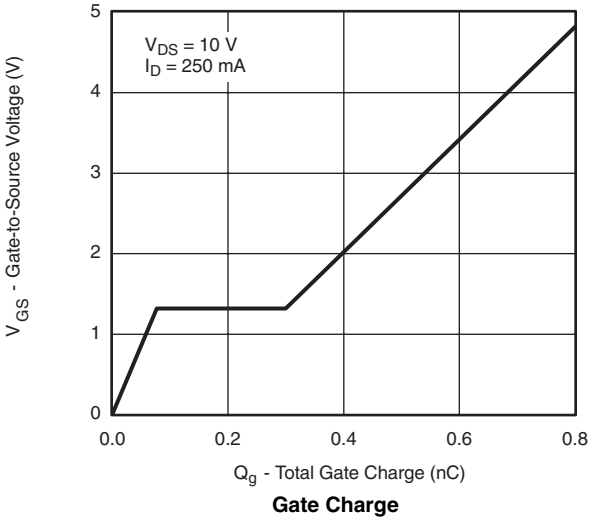
Transfer Characteristics



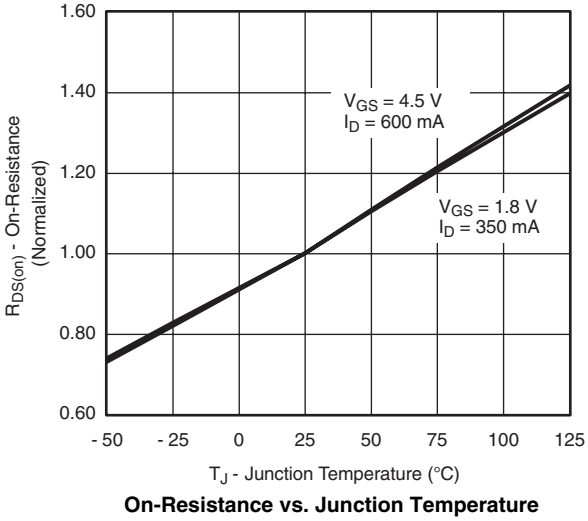
On-Resistance vs. Drain Current



Capacitance

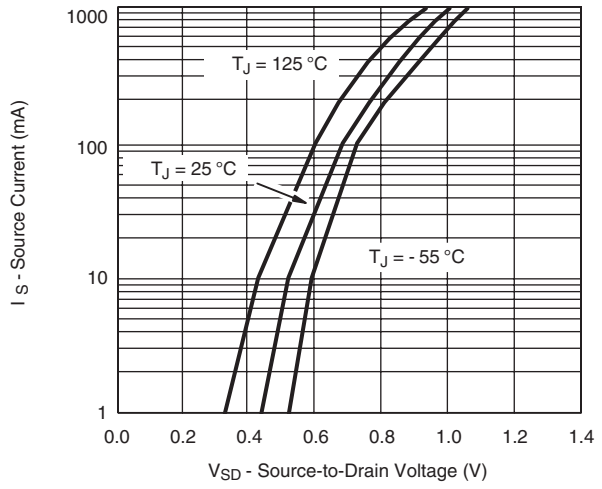


Gate Charge

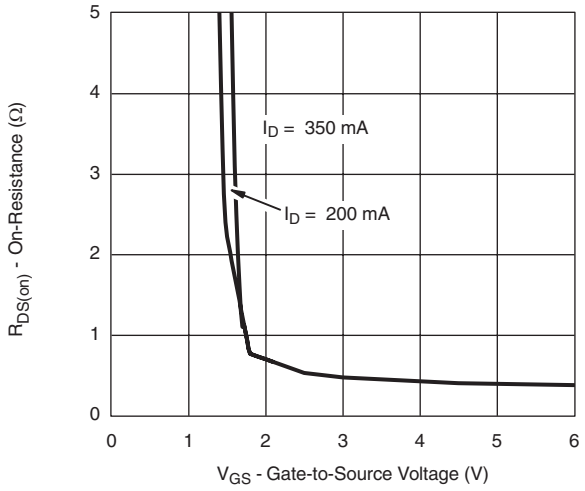


On-Resistance vs. Junction Temperature

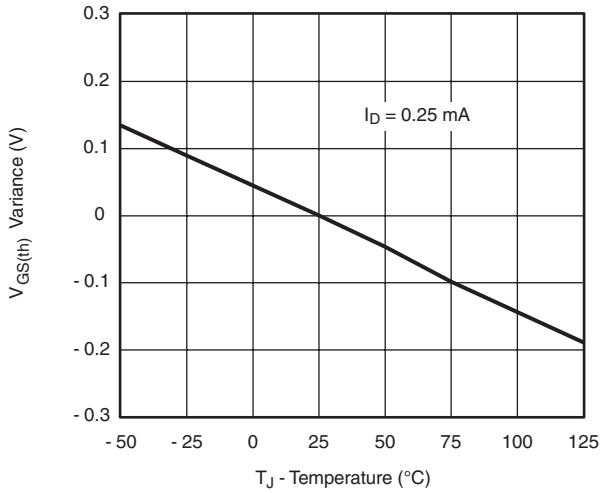
TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



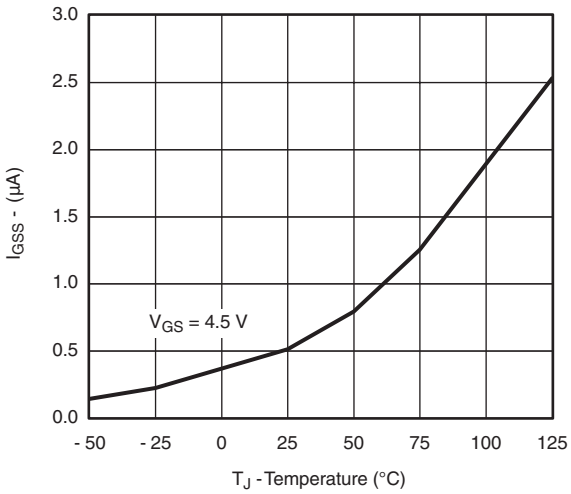
Source-Drain Diode Forward Voltage



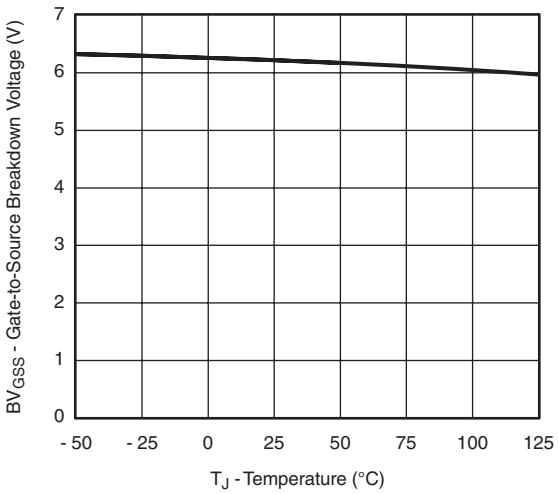
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage Variance vs. Temperature

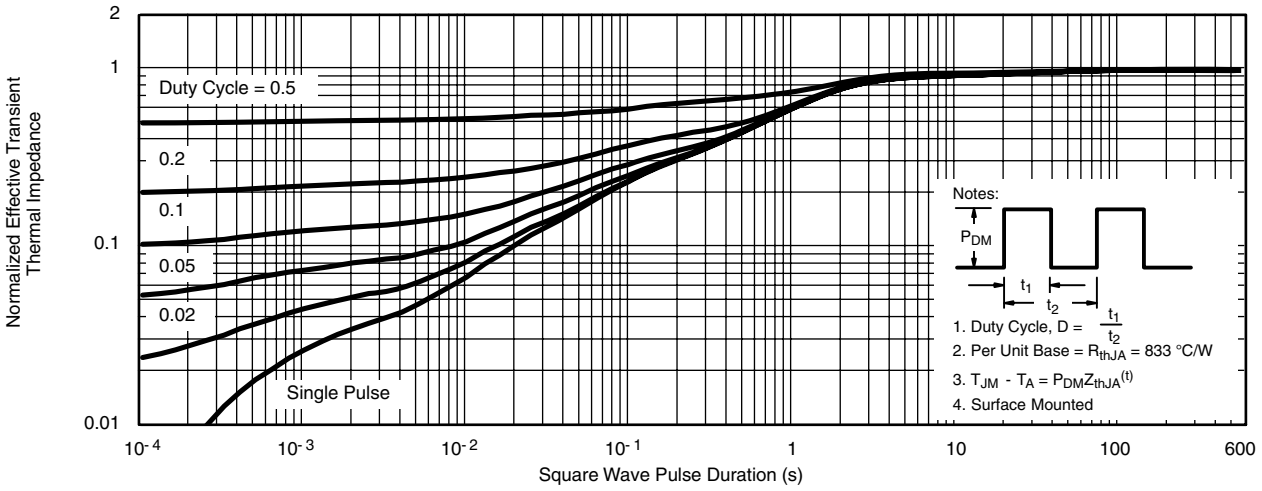


I_{GSS} vs. Temperature

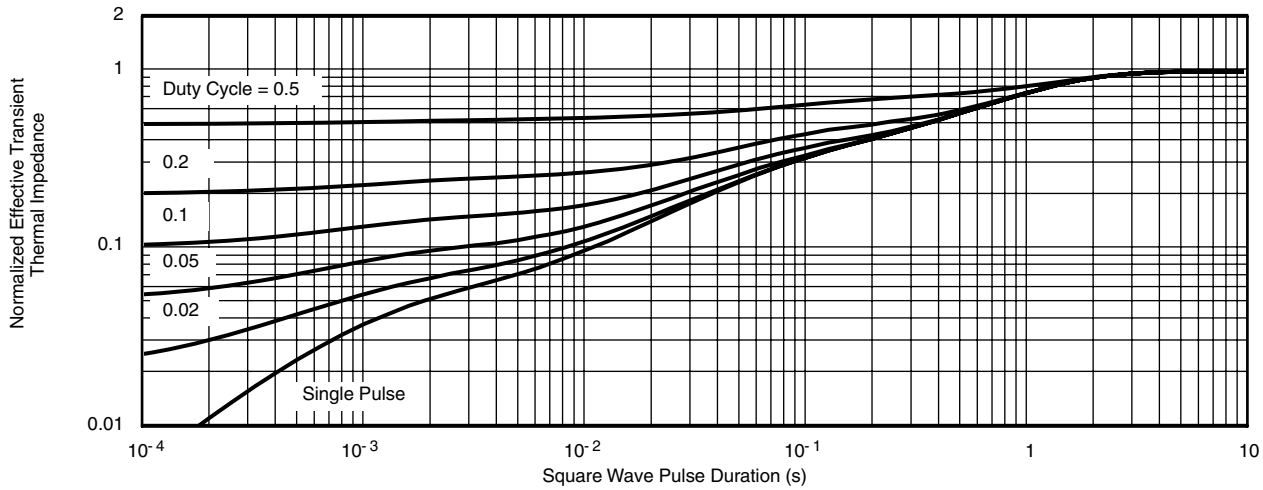


BV_{GSS} vs. Temperature

TYPICAL CHARACTERISTICS T_A = 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient (SC-75A)



Normalized Thermal Transient Impedance, Junction-to-Foot

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